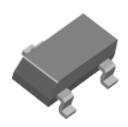
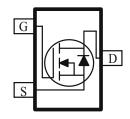
## N-Channel 40V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY					
$V_{DS}(V)$	$I_{D}(A)$				
40	$0.086 @V_{CS} = 10 V$	1.7			
	$0.128 @V_{CS} = 4.5V$	1.4			

- Low r<sub>DS(on)</sub> provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SC70-3 saves board space
- Fast switching speed
- High performance trench technology





ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Maximum	Units			
Drain-Source Voltage		$V_{DS}$	40	V		
Gate-Source Voltage		$V_{cs}$	±20	V		
	T <sub>A</sub> =25°C	T_	1.7			
Continuous Drain Current <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	1D	1.4	A		
Pulsed Drain Current <sup>b</sup>			±20			
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	1.6	A		
D : a	T <sub>A</sub> =25°C	D	0.34	W		
Power Dissipation <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	PD	0.22	VV		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
M · I · · · a	t <= 5 sec	D	100	00/11/		
Maximum Junction-to-Ambient <sup>a</sup>	Steady-State	$R_{THJA}$	166	C/W		

### Notes

**PRELIMINARY** 

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

D 4		T C. 1111	Limits			<b>T.</b>	
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1			V	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 32 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Drain Current	<sup>1</sup> DSS	$V_{DS} = 32 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10		
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	10			A	
Drain-Source On-Resistance <sup>A</sup>	r <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, I_D = 1.7 \text{ A}$			86	mΩ	
Diam-Source On-Resistance		$V_{GS} = 4.5 \text{ V}, I_D = 1.4 \text{ A}$			128		
Forward Tranconductance <sup>A</sup>	$g_{\mathrm{fs}}$	$V_{DS} = 10 \text{ V}, I_{D} = 1.7 \text{ A}$		11.3		S	
Diode Forward Voltage	$V_{\mathrm{SD}}$	$I_S = 1.6 \text{ A}, V_{GS} = 0 \text{ V}$		0.75		V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_{g}$			7.5			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 10 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 1.7 \text{ A}$		0.6		пC	
Gate-Drain Charge	$Q_{gd}$			1.0			
Turn-On Delay Time	t <sub>d(on)</sub>			8			
Rise Time	t <sub>r</sub>	$V_{DD} = 10 \text{ V}, R_L = 15 \Omega, I_D = 1 \text{ A},$		24			
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GEN} = 4.5 \text{ V}$		35		ns	
Fall-Time	t <sub>f</sub>			10		1	

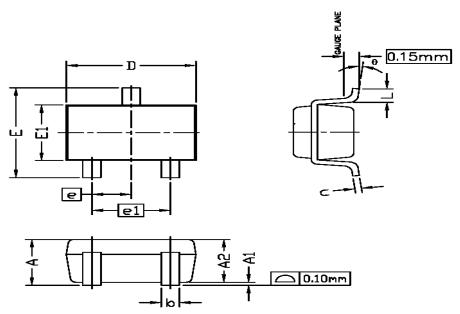
#### Notes

- a. Pulse test:  $PW \le 300us duty cycle \le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

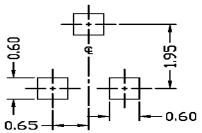
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# Package Information

SC70 PACKAGE OUTLINE



### RECOMMENDED LAND PATTERN



TI	N	IT:	-	ım

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
31,4150125	MIN	NOM	MAX	MIN	NOM	MAX
Α			1.10			0.043
A1	0.00		0.10	0.00		0.004
A2	0.7	0.9	1.00	0.028	0.035	0.039
ь	0.15		0.30	0.006		0.012
c	0.08		0.22	0.003		0.009
D	1.85	2.10	2,15	0.073	0.083	0.085
E	1.80	2.30	2.40	0.071	0.091	0.094
e	0.65 BSC			0.026 BSC		
el	1.30 BSC			0.051 BSC		
<b>E</b> 1	1.1	1.30	1.4	0.043	0.051	0.055
L	0.26	0.36	0.46	0.010	0.014	0.018
θ	0°	4°	80	O°	4°	8°
					_	

### NOTE

- 1. ALL DIMENSIONS ARE IN MILLMETERS.
- 2. DIMENSIONS ARE INCLUSIVE OF PLATING.
- 3. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
  MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 3 MILS EACH.
- DIE IS FACING UP FOR MOLD AND FACING DOWN FOR TRIM/FORM. ie: REVERSE TRIM/FORM.
- 5. DIMENSION L IS MEASURED IN GAUGE PLANE.
- 6. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.